

Min-Kyu Joo

List of Publications by Year in descending order

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43
papers

1,033
citations

471509

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docs citations

43
times ranked

1826
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-frequency noise in multilayer MoS ₂ field-effect transistors: the effect of high-k passivation. <i>Nanoscale</i> , 2014, 6, 433-441.	5.6	146
2	Near-zero hysteresis and near-ideal subthreshold swing in h-BN encapsulated single-layer MoS ₂ field-effect transistors. <i>2D Materials</i> , 2018, 5, 031001.	4.4	104
3	Electron Excess Doping and Effective Schottky Barrier Reduction on the MoS ₂ /h-BN Heterostructure. <i>Nano Letters</i> , 2016, 16, 6383-6389.	9.1	78
4	Junction-Structure-Dependent Schottky Barrier Inhomogeneity and Device Ideality of Monolayer MoS ₂ Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 11240-11246.	8.0	57
5	Probing defect dynamics in monolayer MoS ₂ via noise nanospectroscopy. <i>Nature Communications</i> , 2017, 8, 2121.	12.8	56
6	Plasma treatment effect on charge carrier concentrations and surface traps in a-InGaZnO thin-film transistors. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	46
7	Separation of interlayer resistance in multilayer MoS ₂ field-effect transistors. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	46
8	Effect of Intertube Junctions on the Thermoelectric Power of Monodispersed Single Walled Carbon Nanotube Networks. <i>Journal of Physical Chemistry C</i> , 2014, 118, 26454-26461.	3.1	43
9	Thickness-dependent carrier mobility of ambipolar MoTe ₂ : Interplay between interface trap and Coulomb scattering. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	42
10	Understanding Coulomb Scattering Mechanism in Monolayer MoS ₂ Channel in the Presence of h-BN Buffer Layer. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 5006-5013.	8.0	37
11	Suppression of Interfacial Current Fluctuation in MoTe ₂ Transistors with Different Dielectrics. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 19092-19099.	8.0	35
12	High-mobility junction field-effect transistor via graphene/MoS ₂ heterointerface. <i>Scientific Reports</i> , 2020, 10, 13101.	3.3	32
13	Tunable Mobility in Double-Gated MoTe ₂ Field-Effect Transistor: Effect of Coulomb Screening and Trap Sites. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 29185-29192.	8.0	31
14	A dual analyzer for real-time impedance and noise spectroscopy of nanoscale devices. <i>Review of Scientific Instruments</i> , 2011, 82, 034702.	1.3	26
15	Reduced charge fluctuations in individual SnO ₂ nanowires by suppressed surface reactions. <i>Journal of Materials Chemistry</i> , 2012, 22, 24012.	6.7	22
16	Strong Coulomb scattering effects on low frequency noise in monolayer WS ₂ field-effect transistors. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	18
17	Hydrothermal Synthesis of Stable 1T'-WS ₂ and Single-Walled Carbon Nanotube Hybrid Flexible Thin Films with Enhanced Thermoelectric Performance. <i>Energy Technology</i> , 2018, 6, 1921-1928.	3.8	18
18	Evaluation of power generated by thermoelectric modules comprising a p-type and n-type single walled carbon nanotube composite paper. <i>RSC Advances</i> , 2015, 5, 78099-78103.	3.6	17

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19	Probing Distinctive Electron Conduction in Multilayer Rhenium Disulfide. <i>Advanced Materials</i> , 2018, 31, 1805860.	21.0	16
20	Understanding tunable photoresponsivity of two-dimensional multilayer phototransistors: Interplay between thickness and carrier mobility. <i>Applied Physics Letters</i> , 2020, 116, .	3.3	14
21	Drain induced barrier increasing in multilayer ReS ₂ . <i>2D Materials</i> , 2020, 7, 031004.	4.4	13
22	Restricted Channel Migration in 2D Multilayer ReS ₂ . <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 19016-19022.	8.0	13
23	Degradation pattern of black phosphorus multilayer field-effect transistors in ambient conditions: Strategy for contact resistance engineering in BP transistors. <i>Applied Surface Science</i> , 2017, 419, 637-641.	6.1	12
24	Room-Temperature Mesoscopic Fluctuations and Coulomb Drag in Multilayer WSe ₂ . <i>Advanced Materials</i> , 2019, 31, e1900154.	21.0	12
25	Origin of exciplex degradation in organic light emitting diodes: Thermal stress effects over glass transition temperature of emission layer. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	12
26	Controlled surface adsorption of fd filamentous phage by tuning of the <i>p</i> H and the functionalization of the surface. <i>Journal of Applied Physics</i> , 2011, 109, 064701.	2.5	11
27	Coulomb drag transistor using a graphene and MoS ₂ heterostructure. <i>Communications Physics</i> , 2020, 3, .	5.3	11
28	Temperature-Dependent Opacity of the Gate Field Inside MoS ₂ Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 29022-29028.	8.0	7
29	Coulomb scattering mechanism transition in 2D layered MoTe ₂ : effect of high- <i>I_b</i> passivation and Schottky barrier height. <i>Nanotechnology</i> , 2019, 30, 035206.	2.6	7
30	Multiple machine learning approach to characterize two-dimensional nanoelectronic devices via featurization of charge fluctuation. <i>Npj 2D Materials and Applications</i> , 2021, 5, .	7.9	7
31	Effect of interlayer tunneling barrier on carrier transport and fluctuation in multilayer ReS ₂ . <i>Applied Physics Letters</i> , 2020, 117, .	3.3	6
32	Emergence of Quantum Tunneling in Ambipolar Black Phosphorus Multilayers without Heterojunctions. <i>Advanced Functional Materials</i> , 2022, 32, .	14.9	6
33	Hidden surface channel in two-dimensional multilayers. <i>2D Materials</i> , 2022, 9, 035004.	4.4	5
34	Degradation pattern of contact resistance and characteristic trap energy in blue organic light-emitting diodes. <i>Organic Electronics</i> , 2021, 91, 106067.	2.6	4
35	Surface Modulation of Graphene Field Effect Transistors on Periodic Trench Structure. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 18513-18518.	8.0	3
36	Electrothermal Local Annealing via Graphite Joule Heating on Two-Dimensional Layered Transistors. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 25638-25643.	8.0	3

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37	Low-Voltage-Operated Highly Sensitive Graphene Hall Elements by Ionic Gating. ACS Applied Materials & Interfaces, 2019, 11, 4226-4232.	8.0	3
38	Origin of relaxation frequency shift in blue organic light-emitting diodes. Applied Physics Letters, 2020, 117, 103301.	3.3	3
39	Defect spectroscopy of sidewall interfaces in gate-all-around silicon nanosheet FET. Nanotechnology, 2021, 32, 165202.	2.6	3
40	Metal-Contact Improvement in a Multilayer WSe ₂ Transistor through Strong Hot Carrier Injection. ACS Applied Materials & Interfaces, 2021, 13, 2829-2835.	8.0	3
41	Understanding random telegraph noise in two-dimensional BP/ReS ₂ heterointerface. Applied Physics Letters, 2022, 120, 253507.	3.3	3
42	Nitrogen-plasma treatment of parallel-aligned SnO ₂ -nanowire field-effect transistors. Journal of the Korean Physical Society, 2014, 65, 502-508.	0.7	1
43	Impact of Heat Treatment on a Hetero-Stacked MoS ₂ /h-BN Field-Effect Transistor. IEEE Electron Device Letters, 2019, 40, 1626-1629.	3.9	1